EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1	("6791104").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/11/07 17:57
L2	1	1 and (InAsN InGaAsN GaInAsN indium gallium arsenic arsenide nitride nitrogen).clm.	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/11/07 17:58
L4	3	(US-20040051113-$ or US-20040099856-$).did. or (US-6621842-$ or US-5509026-$ or US-6150604-$).did.	US-PGPUB; USPAT	OR	OFF	2006/11/07 18:17
L5	1	L4 and (GaInP or InGaP)	US-PGPUB; USPAT	OR	OFF	2006/11/07 18:17
L6	89	"5689123"	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2006/11/07 18:17
L7	24	L6 and laser and active near4 (N nitrogen)	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2006/11/07 18:17
L8	13	("20030123511" | "20040161005" | "4703488" | "5218613" | "5276698" | "5767535" | "5900642" | "6434180" | "6546031" | "6711195" | "6785311" | "6791104" | "6801558").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/11/07 18:17
L9	13	L8 and @ad<"20040205"	US-PGPUB; USPAT; USOCR	OR	OFF	2006/11/07 18:17
L10	1	("6810056").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/11/07 18:17
L11	1	("6791104").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/11/07 18:17
L12	1	("20030118068").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/11/07 18:17
L13	101	InGaAsN and InP adj substrate	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2006/11/07 18:17

L14	7	(US-20030026306-$ or US-20020176465-$ or US-20040084667-$ or US-20010048111-$ or US-20030007538-$ or US-20030118068-$ or US-20030118067-$).did.	US-PGPUB	OR	OFF	2006/11/07 18:17
L15	1	L13 and L14	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2006/11/07 18:17
L16	4370	strain with per$1cent	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2006/11/07 18:17
L17	5955	(antimony antimonide) with (nitrogen nitride)	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2006/11/07 18:17
L18	1536	L17 and laser	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2006/11/07 18:17
L19	1	("20030026306").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/11/07 18:17
L20	1	("20020176465").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/11/07 18:17
L21	769	(257/14).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/11/07 18:17
L22	1956424	(strained strainING compressed compression tensile tension) NOT STRAIN	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/11/07 18:17
L23	180	(InAsN or InGaAsN or GaAsN) with (well barrier)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/11/07 18:17

L24	601	(InAsN or GaInAsN or GaAsN)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/11/07 18:17
L25	208	L24 not L23	US-PGPUB; USPAT	OR	OFF	2006/11/07 18:17
L26	941	(InAsSb or GaInAsSb or GaAsSb)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/11/07 18:17
L27	192	(InAsSb or InGaAsSb or GaAsSb) with (well barrier)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/11/07 18:17
L28	633	L26 not L27	US-PGPUB; USPAT	OR	OFF	2006/11/07 18:17
L29	43	(strain mismatch mis-match) with (per$1cent per adj cent) with lattice same defect	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	ON	2006/11/07 18:17
L30	1031	(InAsSb or InGaAsSb or GaAsSb)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/11/07 18:17
L31	810	(InAsN or InGaAsN or GaAsN)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/11/07 18:17
L32	94	L31 SAME L30	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/11/07 18:17
L33	33	L32 and InP near3 substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/11/07 18:17
L34	12	L33 and strain	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/11/07 18:17

L35	49	L23 and L27	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/11/07 18:17
L36	28	L35 and InP near3 substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/11/07 18:17
L37	12	L36 and strain	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/11/07 18:17
L38	9	L34 and @ad<"20040205"	US-PGPUB; USPAT; USOCR	OR	OFF	2006/11/07 18:17
L39	273	InP and (InAsN or InGaAsN)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/11/07 18:17
L40	4	L9 and InP near3 substrate	US-PGPUB; USPAT; USOCR	OR	OFF	2006/11/07 18:17
L41	2	L40 and L39	US-PGPUB; USPAT	OR	OFF	2006/11/07 18:17
L42	1	("20010048111").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/11/07 18:17
L43	1	L42 and (well active)	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2006/11/07 18:17
L44	6	(US-20030013224-$ or US-20030136957-$ or US-20040051113-$ or US-20040079408-$ or US-20040099856-$ or US-20050173694-$).did. or (US-5509026-$ or US-6150604-$ or US-6621842-$ or US-6472680-$ or US-6617618-$ or US-6927412-$).did.	US-PGPUB; USPAT	OR	OFF	2006/11/07 18:17
L45	5	L44 and InP near3 substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/11/07 18:17

L46	77	L6 and laser	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2006/11/07 18:17
L47	20	L32 AND L22	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/11/07 18:17
L48	1	(US-5509026-$).did.	USPAT	OR	OFF	2006/11/07 18:17
L49	1	L10 and InP	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2006/11/07 18:17
L50	39	L28 and L25	US-PGPUB; USPAT	OR	OFF	2006/11/07 18:17
L51	3	L34 not L38	US-PGPUB; USPAT; USOCR	OR	OFF	2006/11/07 18:17
L52	62	strain with per$1cent with lattice	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2006/11/07 18:17
L53	1	(US-6791104-$).did.	USPAT	OR	OFF	2006/11/07 18:17
L54	1	L53 and (InAsN or InNAs or InGaAsN or GaInAsN or InGaNAs or GaInNAs)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/11/07 18:17
L55	2	("20030013224" or "6798809") and InP near3 substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/11/07 18:17
L56	1	L1 and (InAsN or InGaAsN)	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2006/11/07 18:17
L57	3	"6,791,104"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/11/07 18:17

L58	9	L34 and @ad<"20040205"	US-PGPUB; USPAT; USOCR	OR	OFF	2006/11/07 18:17
L59	5	L44 and (InAsN or InGaAsN or GaInAsN or GaInNAs or InNAs or ·InGaNAs)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/11/07 18:17
L60	7	L38 and well same barrier	US-PGPUB; USPAT; USOCR	OR	OFF	2006/11/07 18:17
L61	51	L17 with laser	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2006/11/07 18:17
L62	30	"electron quantum well" and "hole quantum well"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/11/07 18:17
L63	11	L8 and @ad<"20020926"	US-PGPUB; USPAT; USOCR	OR	OFF	2006/11/07 18:17
L64	33	L32 and InP near3 substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/11/07 18:17
L65	6	L14 not L15	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2006/11/07 18:17
L66	4	L63 and InP near3 substrate	US-PGPUB; USPAT	OR	OFF	2006/11/07 18:17
L67	100	L13 not L15	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2006/11/07 18:17
L68	10	strain with (per$1cent per adj cent) with lattice same defect	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	ON	2006/11/07 18:17

L69	5	L29 and (indium or gallium) and phosphide	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	ON	2006/11/07 18:17
L70	10	L37 and @ad<"20040205"	US-PGPUB; USPAT; USOCR	OR	OFF	2006/11/07 18:17